



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max
200V	25Ω @ V <sub>GS</sub> = 10V	60mA

## Features and Benefits


- Low Input Capacitance
- Low Input/Output Leakage

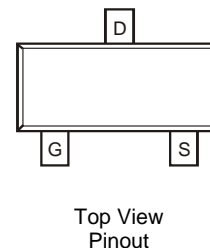
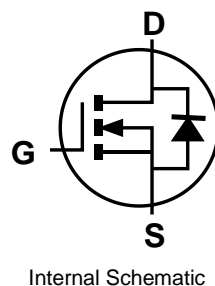
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Battery-operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

## Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	200	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	60	mA
Maximum Body Diode Forward Current	I <sub>S</sub>	60	mA
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	1	A
Pulsed Source Current (10μs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	1	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	330	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	380	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	200	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	10 50	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>A</sub> = +125°C
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
On-State Drain Current	I <sub>D(on)</sub>	250	—	—	mA	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 25V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	17	25	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 100mA
Forward Transconductance	g <sub>fs</sub>	75	—	—	mS	V <sub>DS</sub> = 25V, I <sub>D</sub> = 100mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	—	45	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	18		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	5		
Turn-On Delay Time (Note 8)	t <sub>D(on)</sub>	—	—	5	ns	V <sub>DS</sub> = 25V, I <sub>D</sub> = 100mA
Turn-On Rise Time (Note 8)	t <sub>r</sub>	—	—	7		
Turn-Off Delay Time (Note 8)	t <sub>D(off)</sub>	—	—	6		
Turn-Off Fall Time (Note 8)	t <sub>f</sub>	—	—	6		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.

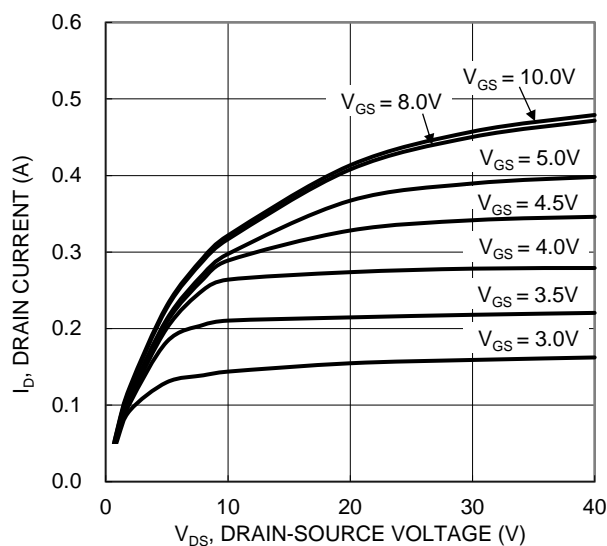


Figure 1. Typical Output Characteristic

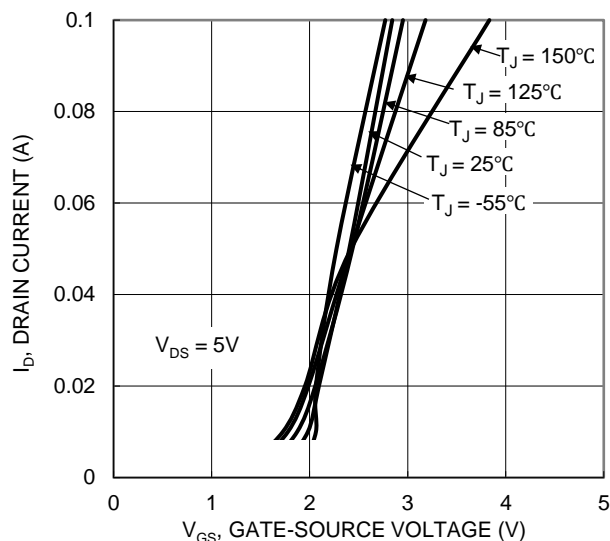


Figure 2. Typical Transfer Characteristic

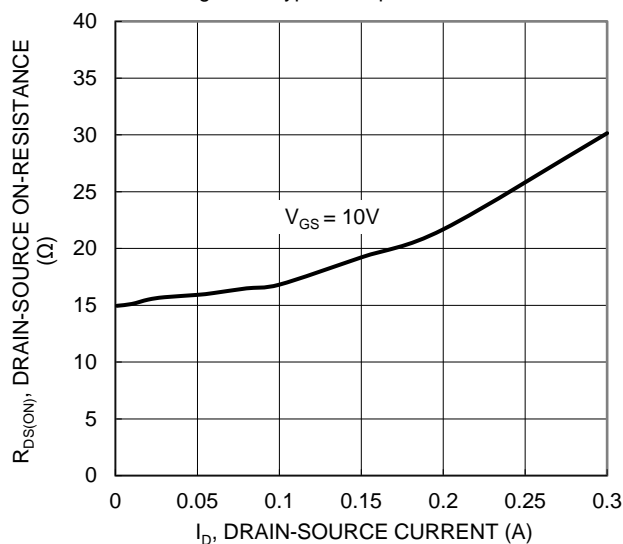


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

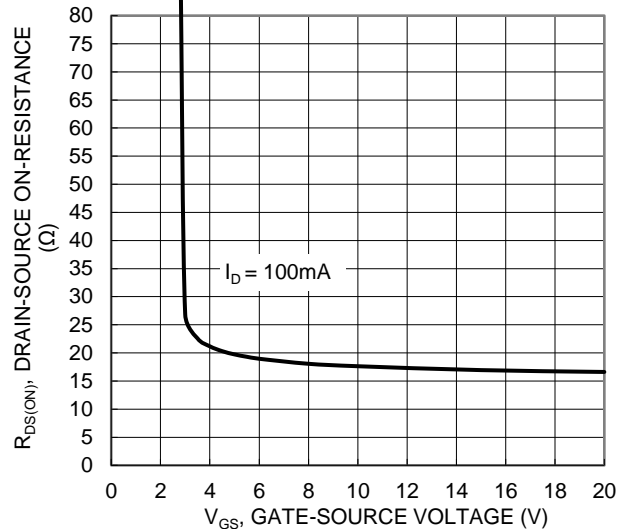


Figure 4. Typical Transfer Characteristic

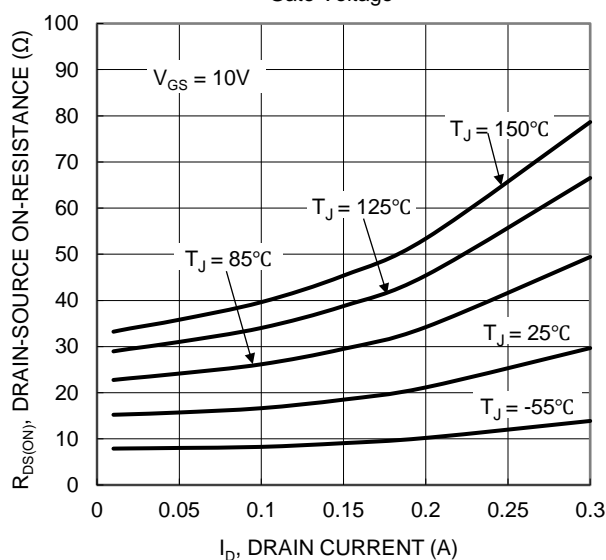


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

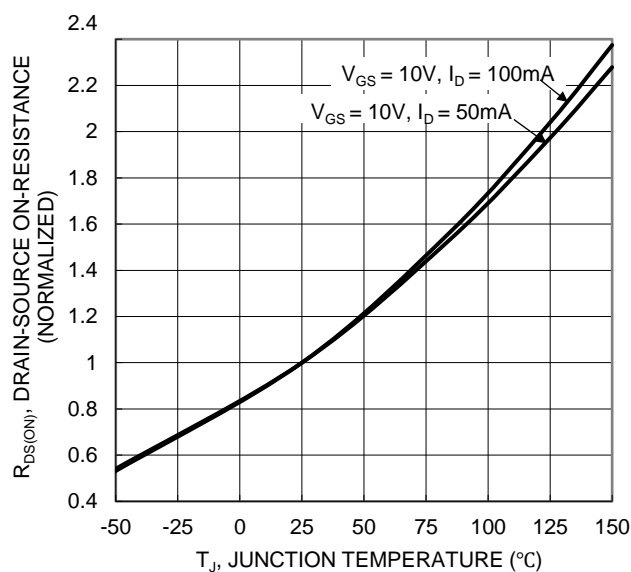


Figure 6. On-Resistance Variation with Temperature

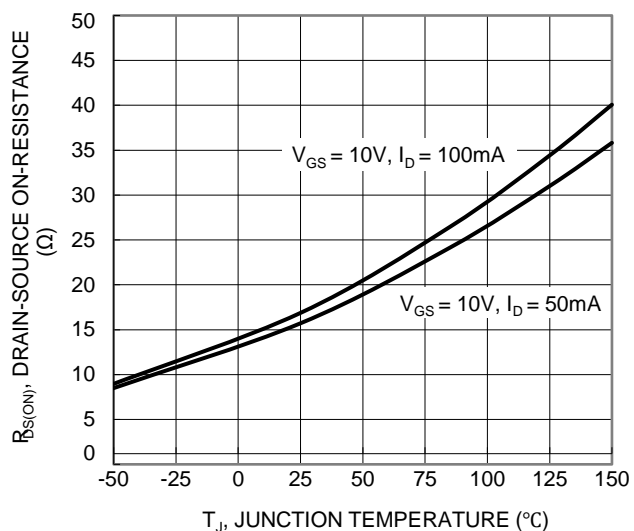


Figure 7. On-Resistance Variation with Temperature

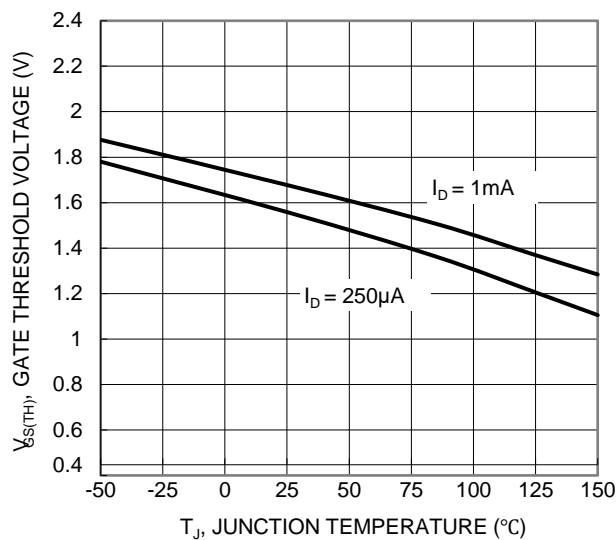


Figure 8. Gate Threshold Variation vs. Junction Temperature

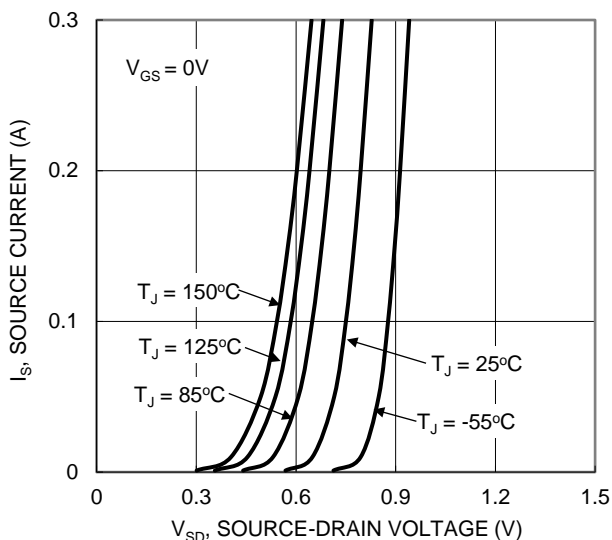


Figure 9. Diode Forward Voltage vs. Current

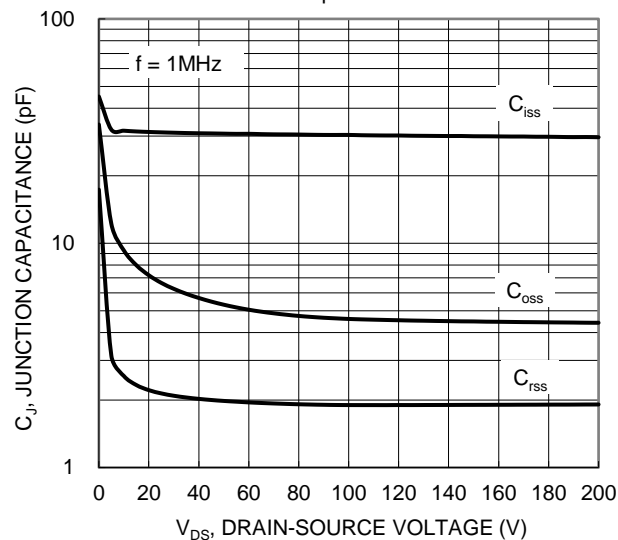


Figure 10. Typical Junction Capacitance

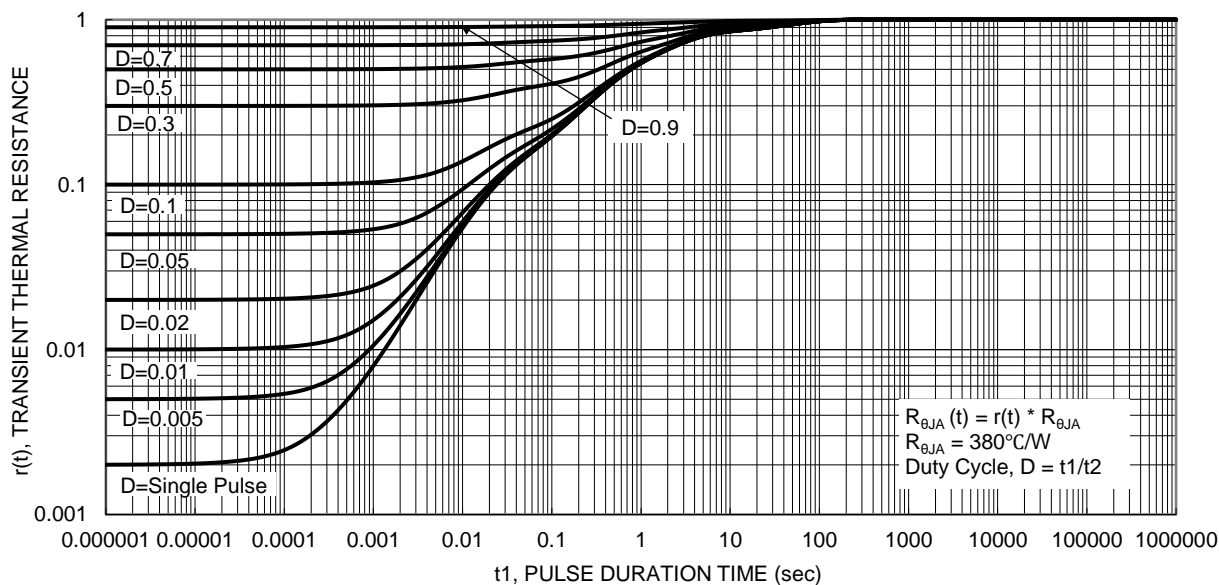
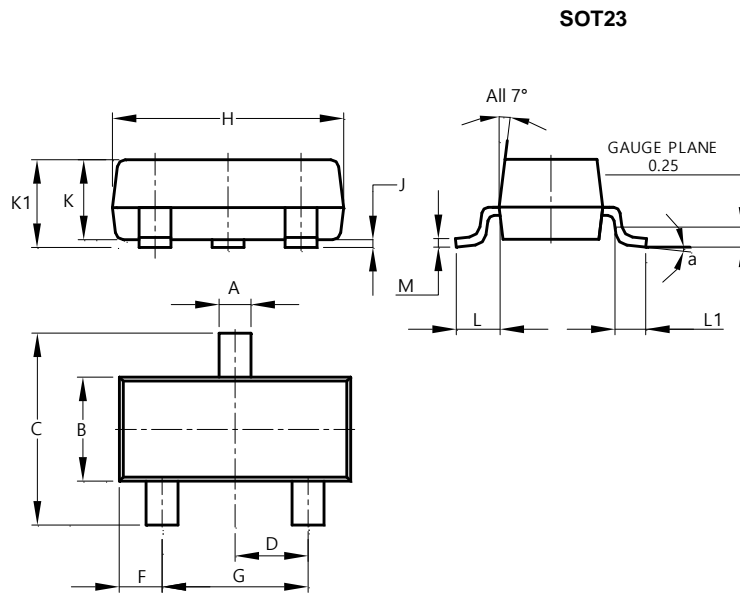


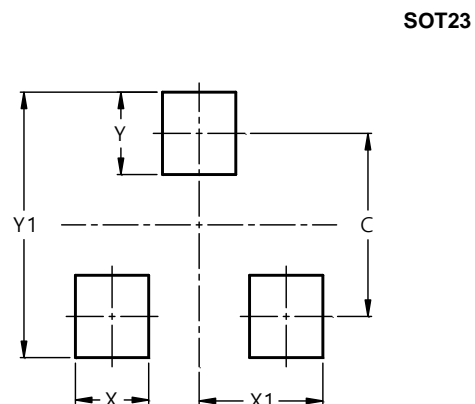
Figure 11. Transient Thermal Resistance

## Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9